

2SD1577

Silicon NPN Triple-Diffused Junction Mesa Type

Horizontal Deflection Output

■ Features

- High breakdown voltage and high reliability by glass passivation
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

■ Absolute Maximum Ratings (Tc=25°C)

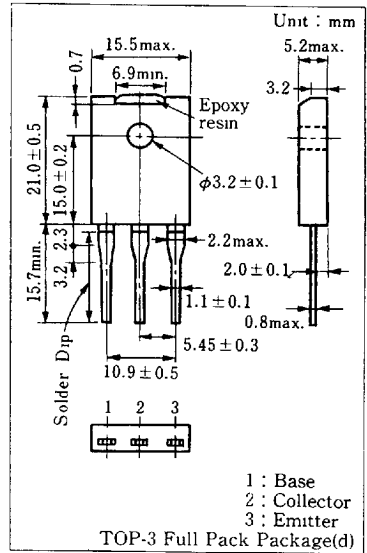
Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	1500	V
Collector-emitter voltage	V_{CES}	1500	V
	V_{CEO}	700	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	5	A
Peak collector current	I_{CP}^*	17	A
Peak base current	I_{BP}	3.5	A
Reverse peak base current	I_{BP}	-2.5	A
Collector power dissipation	$T_c=25^\circ\text{C}$	P_C 100	W
	$T_a=25^\circ\text{C}$	3	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

* Non-repetitive peak value

■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB}=750\text{ V}, I_E=0$			50	μA
		$V_{CB}=1500\text{ V}, I_E=0$			1	mA
Emitter-base voltage	V_{EBO}	$I_E=1\text{ mA}, I_C=0$	6			V
DC current gain	h_{FE}	$V_{CE}=10\text{ V}, I_C=4\text{ A}$	4		15	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=4.5\text{ A}, I_B=2\text{ A}$			2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=4.5\text{ A}, I_B=2\text{ A}$			1.3	V
Transition frequency	f_T	$V_{CE}=10\text{ V}, I_C=0.5\text{ A}, f=0.5\text{ MHz}$		2		MHz
Fall time	t_f	$I_C=4\text{ A}, I_{Bend}=1.5\text{ A}$			1	μS
Storage time	t_{stg}	$L_B=10\text{ }\mu\text{H}$			11	μS

■ Package Dimensions



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